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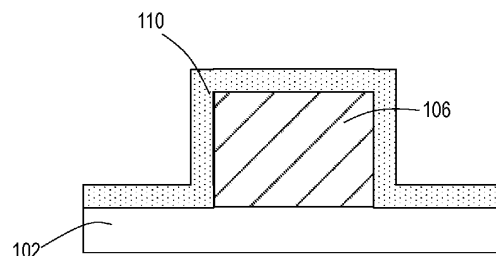


FIG. 1B

(57) Abstract: Methods for depositing a silicon germanium tin boron (SiGeSn:B) film on a substrate are described. The method comprises exposing a substrate to a precursor mixture comprising a boron precursor, a silicon precursor, a germanium precursor, and a tin precursor to form a boron silicon germanium tin (SiGeSn:B) film on the substrate.



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